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### FAIRCHILD

SEMICONDUCTOR®

November 2013

## **FQB55N10 N-Channel QFET® MOSFET**

100 V, 55 A, 26 mΩ

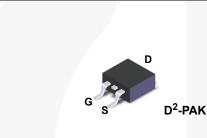
### Description

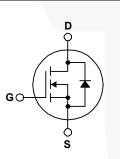
This N-Channel enhancement mode power MOSFET is • 55 A, 100 V,  $R_{DS(on)}$  = 26 m $\Omega$  (Max.) @ V<sub>GS</sub> = 10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state D = 27.5 A Low Gate Charge (Typ. 75 nC) resistance, and to provide superior switching performance • Low Crss (Typ. 130 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power • 100% Avalanche Tested factor correction (PFC), and electronic lamp ballasts.

#### Features

- I<sub>D</sub> = 27.5 A

- 175°C Maximum Junction Temperature Rating





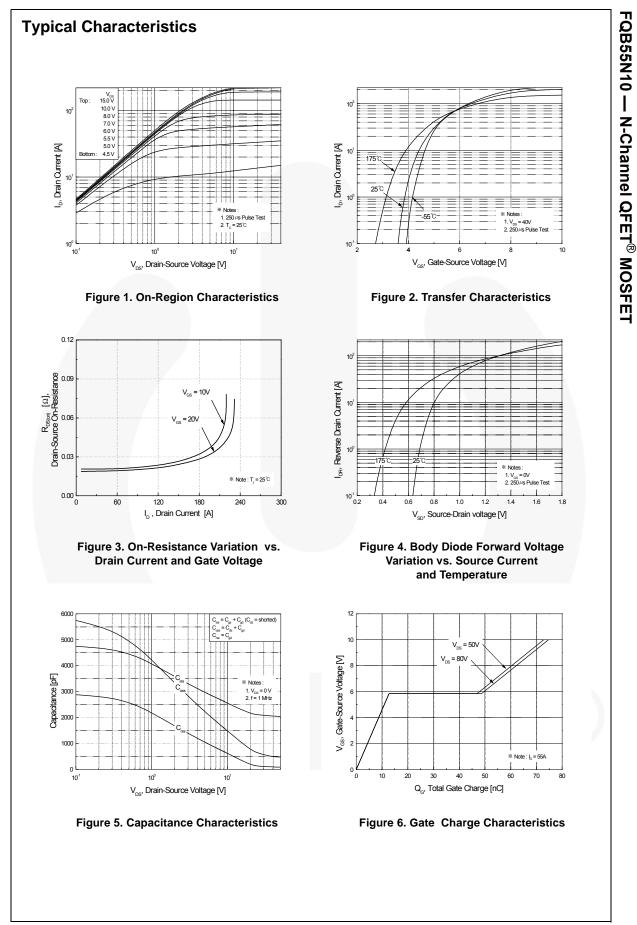
#### Absolute Maximum Ratings T<sub>c</sub> = 25°C unless otherwise noted.

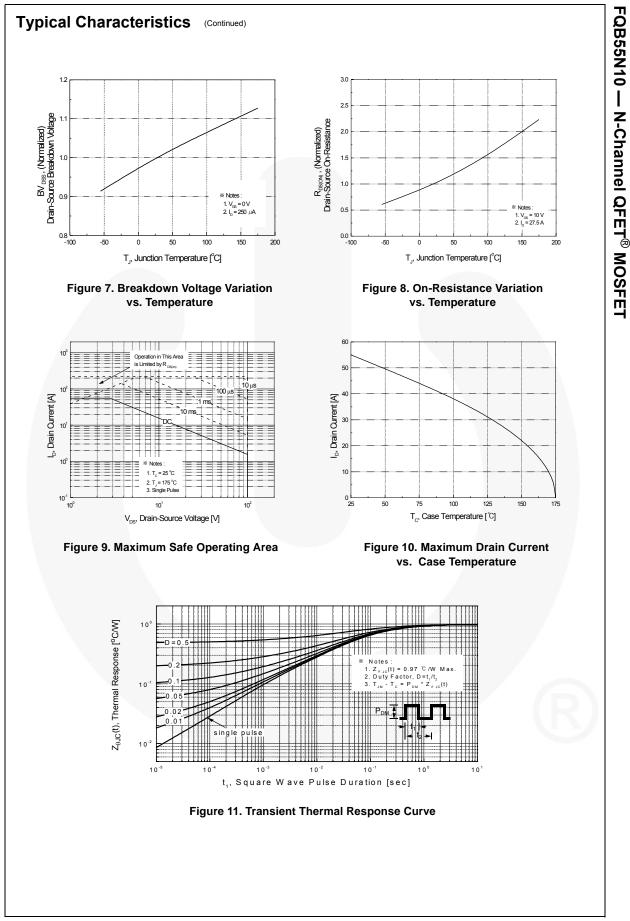
Symbol	Parameter	FQB55N10TM	Unit	
V <sub>DSS</sub>	Drain-Source Voltage	100	V	
ID	Drain Current - Continuous ( $T_C = 25^{\circ}C$ )	55	A	
	- Continuous (T <sub>C</sub> = 100°C)	38.9	A	
I <sub>DM</sub>	Drain Current - Pulsed (Note 1)	220	A	
V <sub>GSS</sub>	Gate-Source Voltage	± 25	V	
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)	1100	mJ	
I <sub>AR</sub>	Avalanche Current (Note 1)	55	A	
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1)	15.5	mJ	
dv/dt	Peak Diode Recovery dv/dt (Note 3)	6.0	V/ns	
P <sub>D</sub>	Power Dissipation $(T_A = 25^{\circ}C)^{*}$	3.75	W	
	Power Dissipation ( $T_C = 25^{\circ}C$ )	155	W	
	- Derate above 25°C	1.03	W/°C	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to +175	°C	
TL	Maximum lead temperature for soldering,1/8" from case for 5 seconds	300	°C	

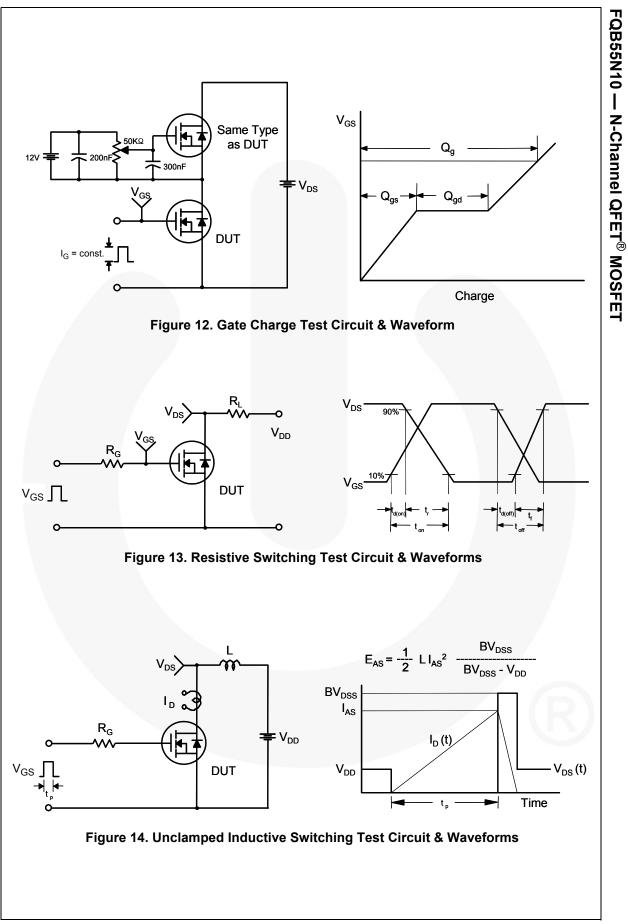
### **Thermal Characteristics**

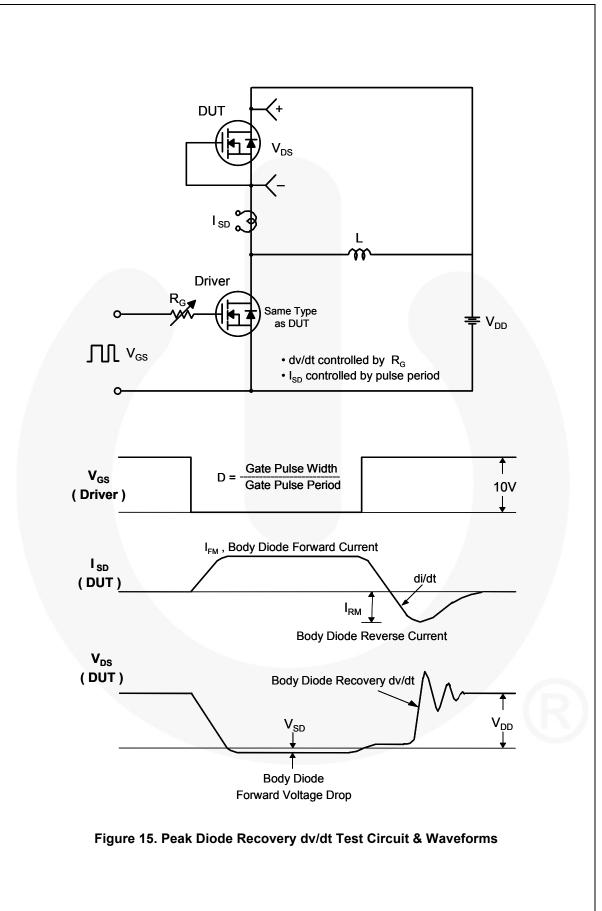
Symbol	Parameter	FQB55N10TM	Unit
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	0.97	
$R_{ hetaJA}$	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	62.5	°C/W
	Thermal Resistance, Junction to Ambient (*1 in <sup>2</sup> Pad of 2-oz Copper), Max.	40	

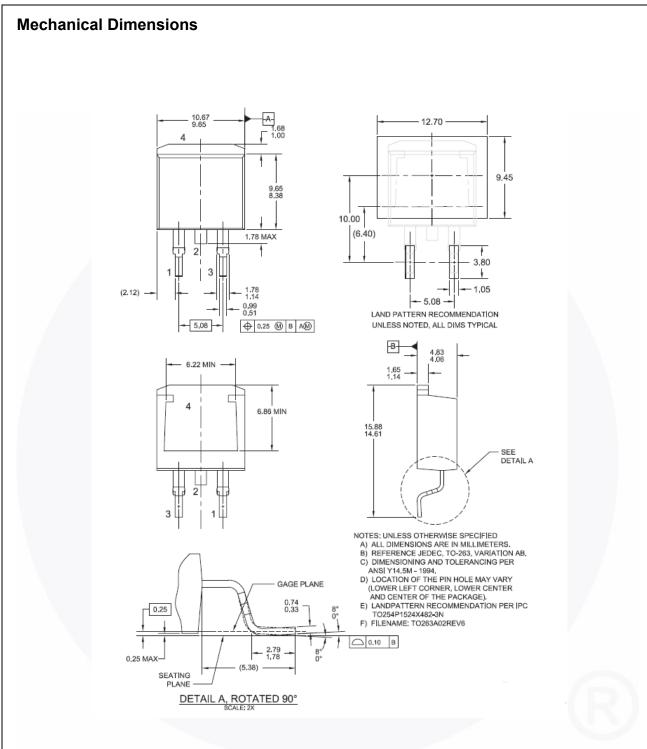
Part Number Top Mark Pa		Pac	kage Packing Method Reel		Size	Tape Width		Quantity			
FQB5	FQB55N10TM FQB55N10 D <sup>2</sup> -		PAK Tape and Reel 330			330	mm	24 mm		800 units	
Electri	cal Cha	racteristics	T <sub>C</sub> = 25°	C unless otl	nerwise noted.						
Symbol		Parameter			Test Conditions			Min.	Тур. Ма		x. Unit
Off Cha	racterist	ics									
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage			$V_{GS}$ = 0 V, I <sub>D</sub> = 250 µA				100			V
$\Delta BV_{DSS}$ / $\Delta T_{J}$	Breakdown Voltage Temperature Coefficient			$I_D = 250 \mu\text{A}$ , Referenced to $25^{\circ}\text{C}$					0.1		V/°C
I <sub>DSS</sub>	Zero Gate	Zero Gate Voltage Drain Current		V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V					1	μA	
				V <sub>DS</sub> = 80 V, T <sub>C</sub> = 150°C					10	μA	
I <sub>GSSF</sub>		y Leakage Current, F		$V_{GS}$ = 25 V, $V_{DS}$ = 0 V						100	nA
I <sub>GSSR</sub>	Gate-Bod	y Leakage Current, R	everse	V <sub>GS</sub> =	-25 V, V <sub>DS</sub> =	0 V				-100	nA
On Cha	racterist	ics									
V <sub>GS(th)</sub>	Gate Thre	Sate Threshold Voltage		V <sub>DS</sub> =	V <sub>GS</sub> , I <sub>D</sub> = 25	0 μΑ		2.0		4.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 27.5 A					0.021	0.026	Ω	
9 <sub>FS</sub>	Forward Transconductance		V <sub>DS</sub> = 40 V, I <sub>D</sub> = 27.5 A				38		S		
Dynami	ic Charad	cteristics									
C <sub>iss</sub>	Input Cap	acitance		V <sub>DS</sub> =	25 V, V <sub>GS</sub> = 0 V, MHz	0 V,			2100	2730	pF
C <sub>oss</sub>	Output Ca	apacitance		f = 1.0					640	830	pF
C <sub>rss</sub>	Reverse 1	Fransfer Capacitance							130	170	pF
Switchi	ng Chara	acteristics									
t <sub>d(on)</sub>	Turn-On Delay Time			V <sub>DD</sub> = 50 V, I <sub>D</sub> = 55 A,				25	60	ns	
t <sub>r</sub>	Turn-On F	Rise Time		$R_G = 2$	-				250	510	ns
t <sub>d(off)</sub>	Turn-Off D	Delay Time			0 11				110	230	ns
t <sub>f</sub>	Turn-Off F	all Time					Note 4)		140	290	ns
Qg	Total Gate	e Charge		V <sub>DS</sub> =	80 V, I <sub>D</sub> = 55	iА,			75	98	nC
Q <sub>gs</sub>	Gate-Sou	rce Charge		V <sub>GS</sub> =		-			13		nC
Q <sub>gd</sub>	Gate-Drai	n Charge		(Note 4					36		nC
Drain-S	ource Di	ode Characteris	tics a	nd Max	imum Ra	tings					
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current							55	A		
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current							220	Α		
V <sub>SD</sub>	Drain-Sou	rce Diode Forward V	oltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 55 A					1.5	V	
t <sub>rr</sub>	Reverse F	Recovery Time		V <sub>GS</sub> = 0 V, I <sub>S</sub> = 55 A,				100		ns	
Q <sub>rr</sub>	Reverse F	Recovery Charge		dl <sub>F</sub> / dt = 100 A/μs					380		nC











### Figure 16. TO263 (D<sup>2</sup>PAK), Molded, 2-Lead, Surface Mount

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FQB55N10 — N-Channel QFET<sup>®</sup> MOSFET



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